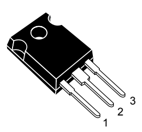
life.augmented

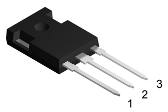
STGW25H120DF2, STGWA25H120DF2

Datasheet

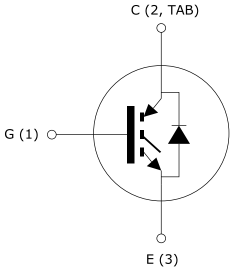
Trench gate field-stop IGBT, H series 1200 V, 25 A high speed



TO-247



TO-247 long leads



STPOWER

Product status links
STGW25H120DF2
STGWA25H120DF2

Product summary	
Order code	STGW25H120DF2
Marking	G25H120DF2
Package	TO-247
Packing	Tube
Order code	STGWA25H120DF2
Marking	G25H120DF2
Package	TO-247 long leads
Packing	Tube

Features

- Maximum junction temperature: T_J = 175 °C
- High speed switching series
- Minimized tail current
- $V_{CE(sat)}$ = 2.1 V (typ.) @ I_C = 25 A
- 5 µs minimum short circuit withstand time at T_J = 150 °C
- Safe paralleling
- Low thermal resistance
- Very fast recovery antiparallel diode

Applications

- Photovoltaic inverters
- Uninterruptible power supply
- Welding
- Power factor correction
- High frequency converters

Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the H series of IGBTs, which represents an optimum compromise between conduction and switching losses to maximize the efficiency of high-switching frequency converters. Furthermore, a slightly positive $V_{CE(sat)}$ temperature coefficient and very tight parameter distribution result in safer paralleling operation.

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage (V_{GE} = 0 V)	1200	V
I_C	Continuous collector current at T_C = 25 °C	50	A
	Continuous collector current at T_C = 100 °C	25	
I_{CP} [(1)]	Pulsed collector current	100	A
V_{GE}	Gate-emitter voltage	±20	V
	Transient gate-emitter voltage (t_p ≤ 10 μs, D ≤ 0.01)	±30	
I_F	Continuous forward current at T_C = 25 °C	50	A
	Continuous forward current at T_C = 100 °C	25	
I_{FP} [(1)]	Pulsed forward current	100	A
P_{TOT}	Total power dissipation at T_C = 25 °C	375	W
T_J	Operating junction temperature range	- 55 to 175	°C
T_{STG}	Storage temperature range	- 55 to 150	°C

1. *Pulse width limited by maximum junction temperature.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case IGBT	0.4	°C/W
	Thermal resistance, junction-to-case diode	1.47	
R_{thJA}	Thermal resistance, junction-to-ambient	50	°C/W

2 Electrical characteristics

T_J = 25 °C unless otherwise specified.

Table 3. Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	V_{GE} = 0 V, I_C = 2 mA	1200			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE} = 15 V, I_C = 25 A		2.1	2.6	V
		V_{GE} = 15 V, I_C = 25 A, T_J = 125 °C		2.4		
		V_{GE} = 15 V, I_C = 25 A, T_J = 175 °C		2.5		
V_F	Forward on-voltage	I_F = 25 A		3.8	4.9	V
		I_F = 25 A, T_J = 125 °C		3.05		
		I_F = 25 A, T_J = 175 °C		2.8		
$V_{GE(th)}$	Gate threshold voltage	V_{CE} = V_{GE}, I_C = 1 mA	5	6	7	V
I_{CES}	Collector cut-off current	V_{GE} = 0 V, V_{CE} = 1200 V			25	µA
I_{GES}	Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = ±20 V			250	nA

Table 4. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	V_{CE} = 25 V, f = 1 MHz, V_{GE} = 0 V	-	2010	-	pF
C_{oes}	Output capacitance		-	146	-	pF
C_{res}	Reverse transfer capacitance		-	49	-	pF
Q_g	Total gate charge	V_{CC} = 960 V, I_C = 25 A, V_{GE} = 0 to 15 V (see Figure 28. Gate charge test circuit)	-	100	-	nC
Q_{ge}	Gate-emitter charge		-	11	-	nC
Q_{gc}	Gate-collector charge		-	52	-	nC

Table 5. **IGBT switching characteristics (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{CE} = 600 V, I_C = 25 A, R_G = 10 Ω, V_{GE} = 15 V (see Figure 27. Test circuit for inductive load switching)		29	-	ns
t_r	Current rise time			12	-	ns
$(di/dt)_{on}$	Turn-on current slope			1774	-	A/µs
$t_{d(off)}$	Turn-off delay time			130	-	ns
t_f	Current fall time			106	-	ns
E_{on}(1)	Turn-on switching energy			0.6	-	mJ
E_{off}(2)	Turn-off switching energy			0.7	-	mJ
E_{ts}	Total switching energy			1.3	-	mJ
$t_{d(on)}$	Turn-on delay time	V_{CE} = 600 V, I_C = 25 A, R_G = 10 Ω, V_{GE} = 15 V, T_J = 175 °C (see Figure 27. Test circuit for inductive load switching)		27.5	-	ns
t_r	Current rise time			13.5	-	ns
$(di/dt)_{on}$	Turn-on current slope			1522	-	A/µs
$t_{d(off)}$	Turn-off delay time			139	-	ns
t_f	Current fall time			200	-	ns
E_{on}(1)	Turn-on switching energy			1.05	-	mJ
E_{off}(2)	Turn-off switching energy			1.65	-	mJ
E_{ts}	Total switching energy			2.7	-	mJ
t_{sc}	Short-circuit withstand time	V_{CE} = 600 V, V_{GE} = 15 V, T_J = 150 °C,	5		-	µs

1. *Including the reverse recovery of the diode.*
2. *Including the tail of the collector current.*

Table 6. **Diode switching characteristics (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	I_F = 25 A, V_R = 600 V, di/dt = 500 A/µs, V_{GE} = 15 V (see Figure 27. Test circuit for inductive load switching)	-	303	-	ns
Q_{rr}	Reverse recovery charge		-	0.93	-	µC
I_{rrm}	Reverse recovery current		-	15.3	-	A
dI_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	400	-	A/µs
E_{rr}	Reverse recovery energy		-	0.52	-	mJ
t_{rr}	Reverse recovery time	I_F = 25 A, V_R = 600 V, di/dt = 500 A/µs, V_{GE} = 15 V, T_J = 175 °C (see Figure 27. Test circuit for inductive load switching)	-	508	-	ns
Q_{rr}	Reverse recovery charge		-	2.71	-	µC
I_{rrm}	Reverse recovery current		-	23		A
dI_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	680		A/µs
E_{rr}	Reverse recovery energy		-	1.56		mJ

2.1 Electrical characteristics (curves)

Figure 1. Power dissipation vs case temperature

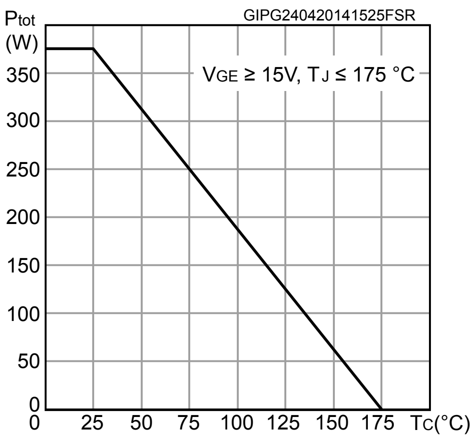


Figure 2. Collector current vs case temperature

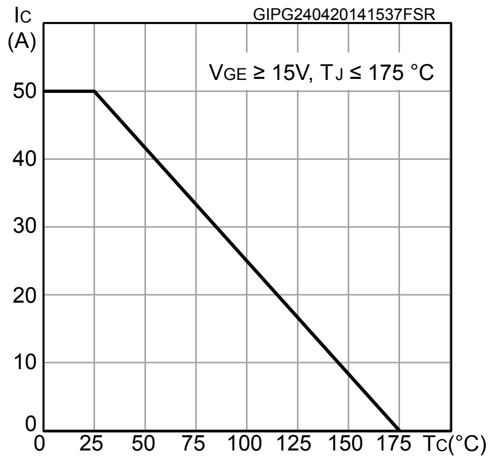


Figure 3. Output characteristics (T_J = 25 °C)

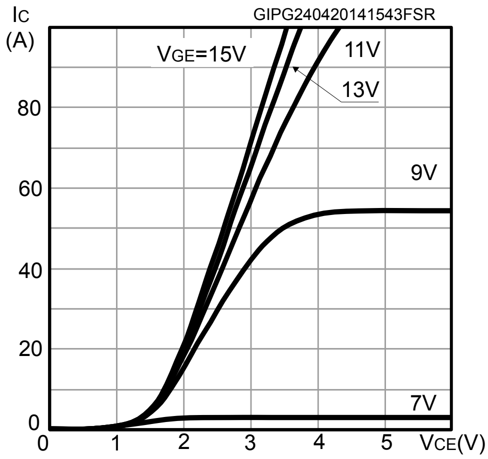


Figure 4. Output characteristics (T_J = 175 °C)

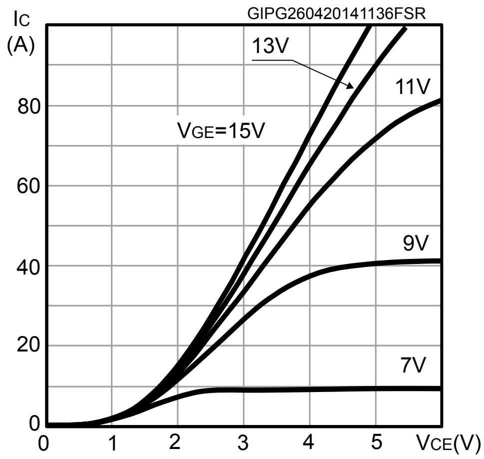


Figure 5. V_{CE}(sat) vs junction temperature

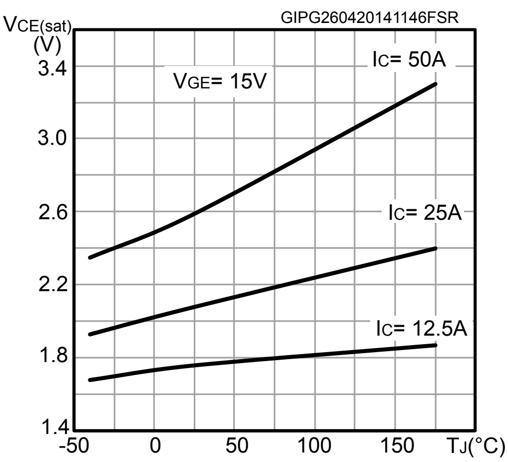


Figure 6. V_{CE}(sat) vs collector current

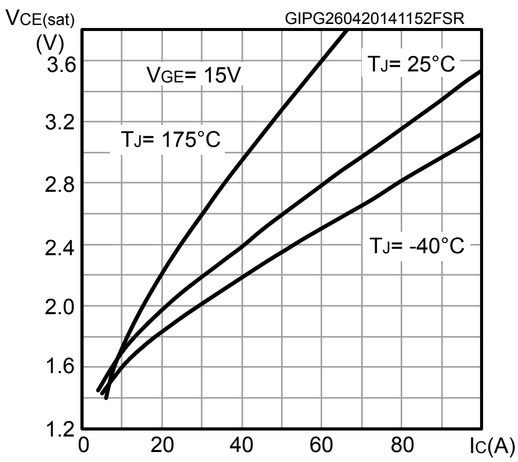


Figure 7. Collector current vs switching frequency

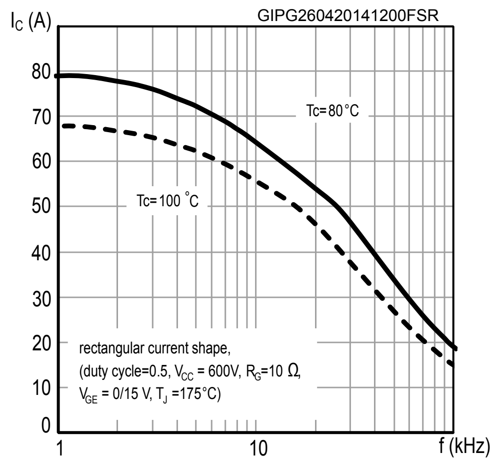


Figure 8. Safe operating area

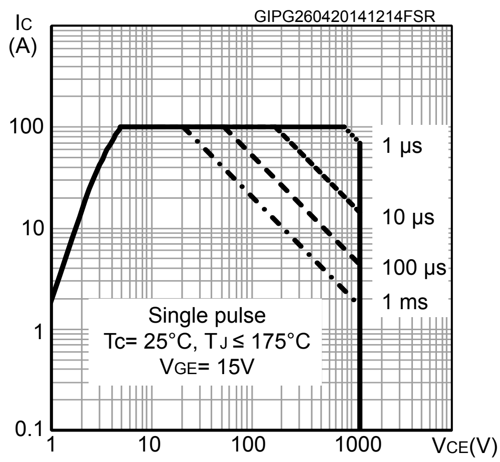


Figure 9. Transfer characteristics

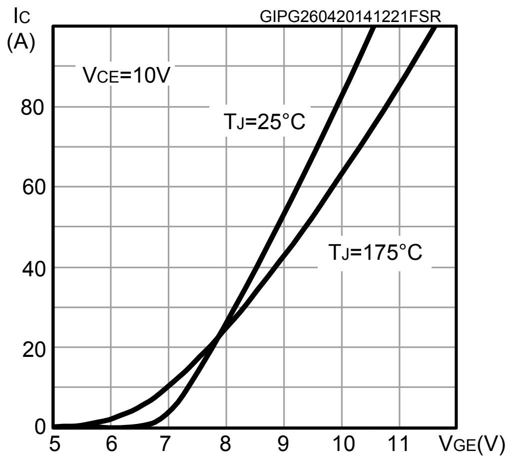


Figure 10. Diode V_F vs forward current

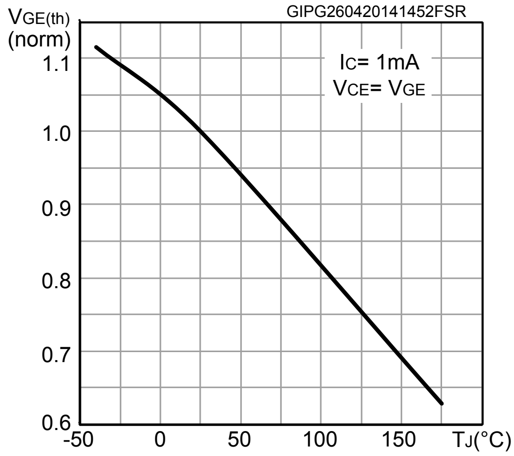


Figure 11. Normalized $V_{(BR)CES}$ vs junction temperature

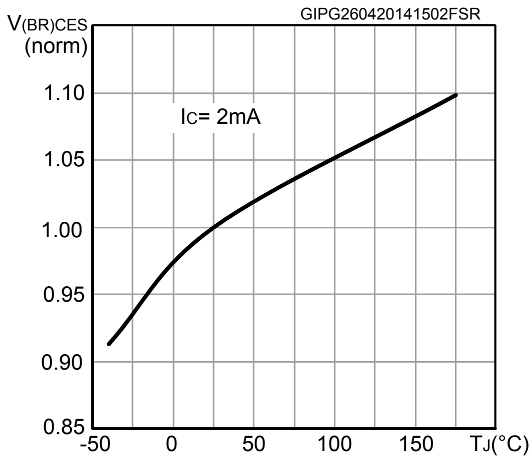


Figure 12. Capacitance variations

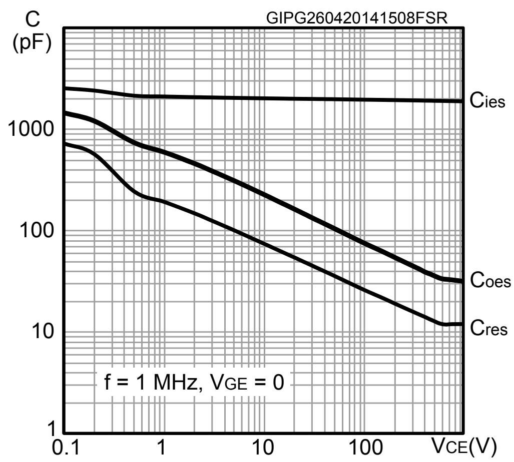


Figure 13. Gate charge vs gate-emitter voltage

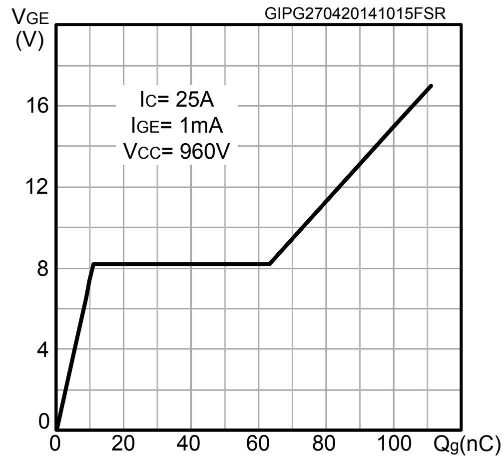


Figure 14. Switching energy vs collector current

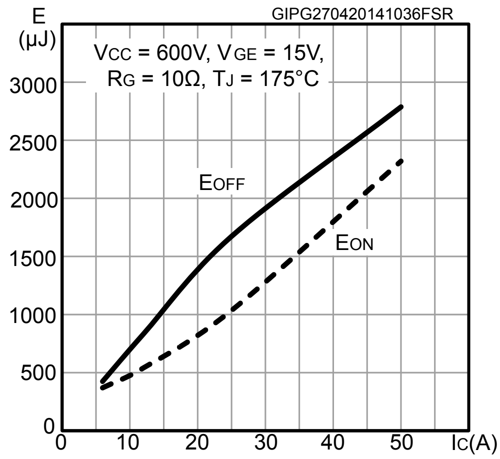


Figure 15. Switching energy vs gate resistance

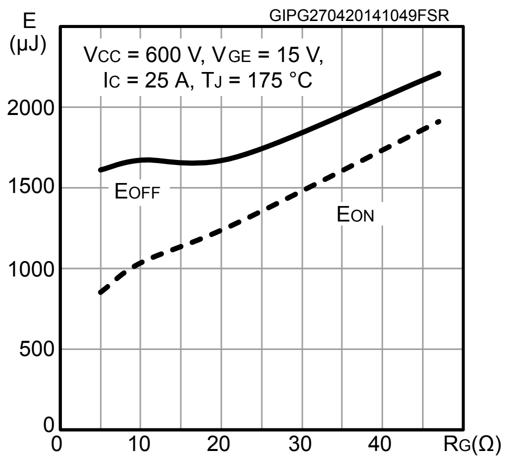


Figure 16. Switching energy vs junction temperature

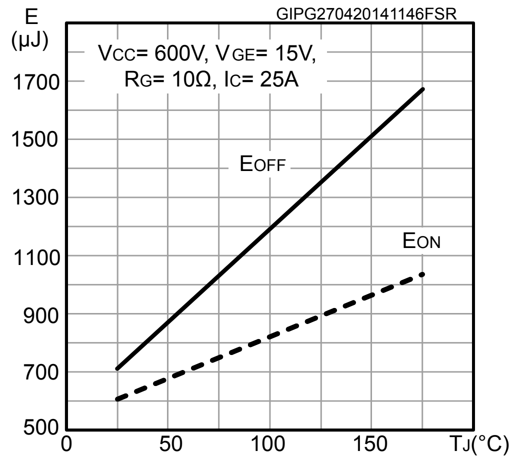


Figure 17. Switching energy vs collector-emitter voltage

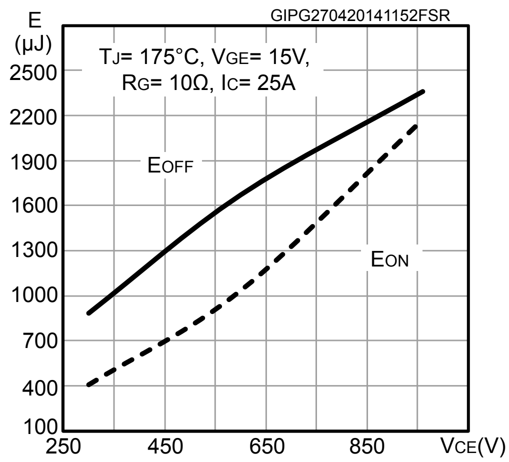


Figure 18. Switching times vs collector current

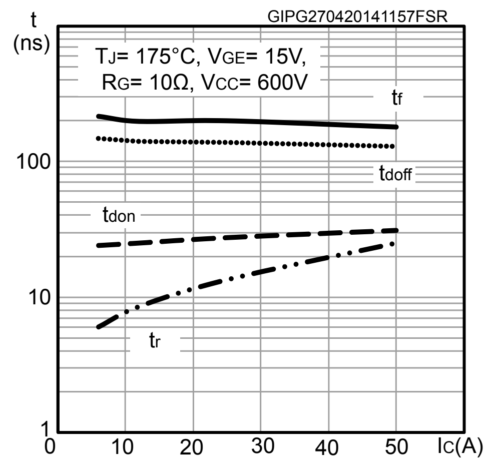


Figure 19. Switching times vs gate resistance

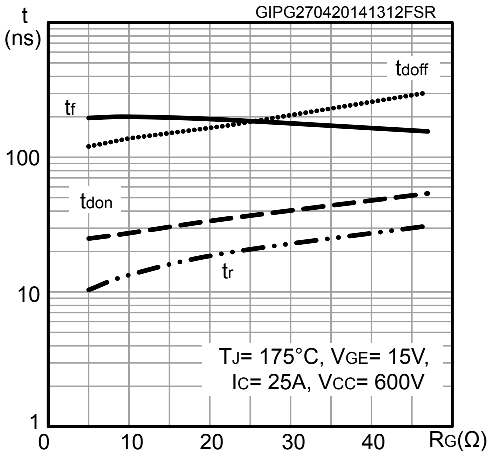


Figure 20. Reverse recovery current vs diode current slope

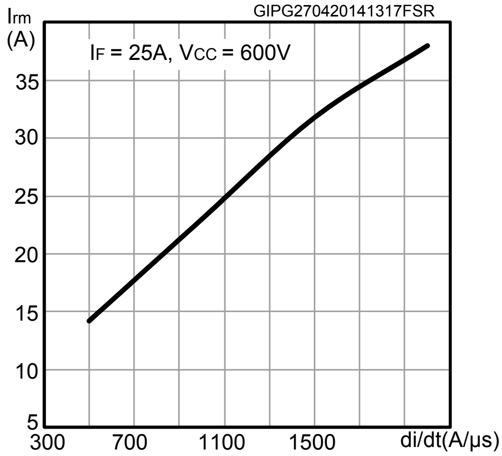


Figure 21. Reverse recovery time vs diode current slope

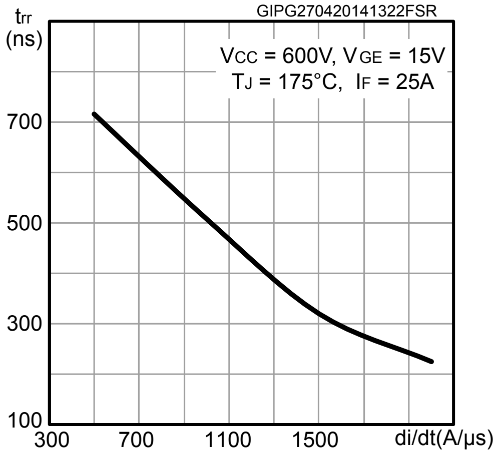


Figure 22. Reverse recovery charge vs diode current slope

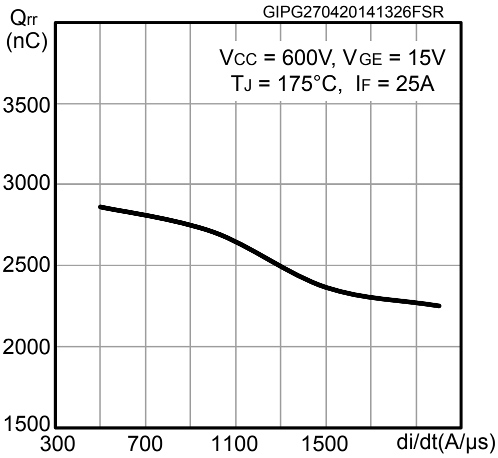


Figure 23. Reverse recovery energy vs diode current slope

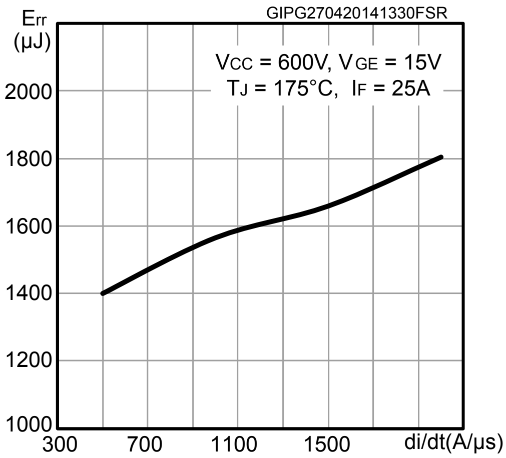


Figure 24. Diode V_F vs forward current

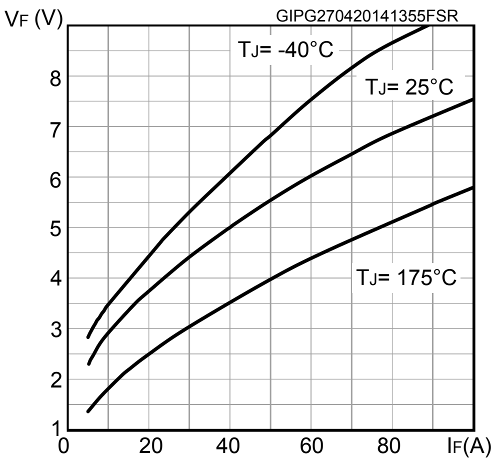


Figure 25. **Thermal impedence for IGBT**

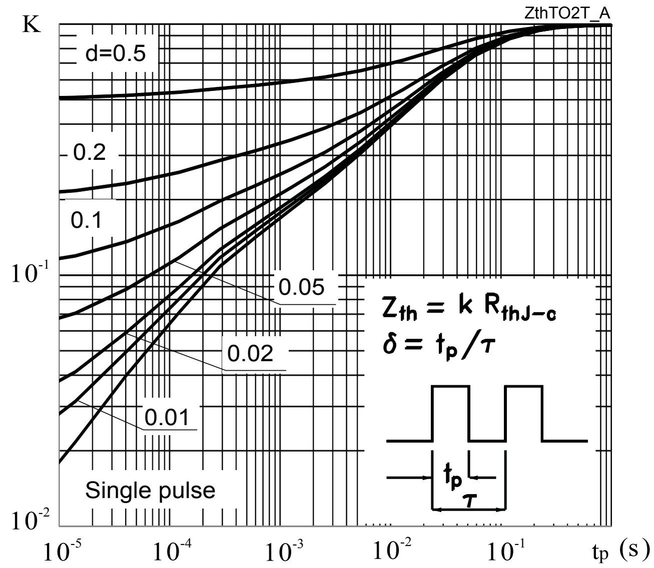
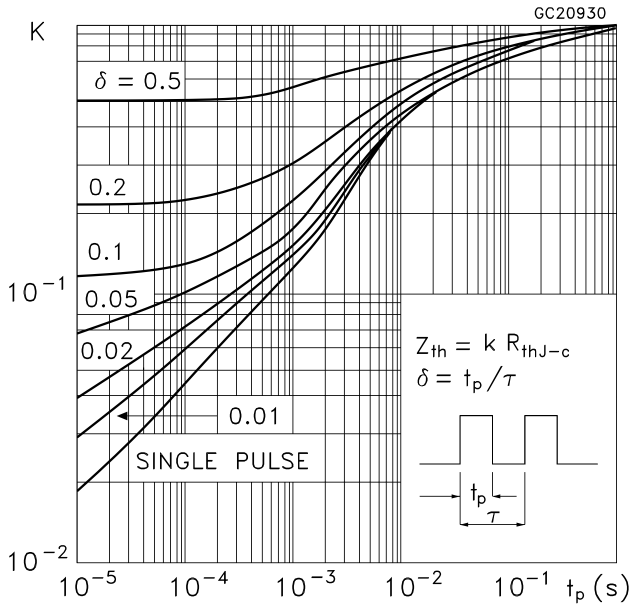


Figure 26. **Thermal impedance for diode**



3 Test circuits

Figure 27. Test circuit for inductive load switching

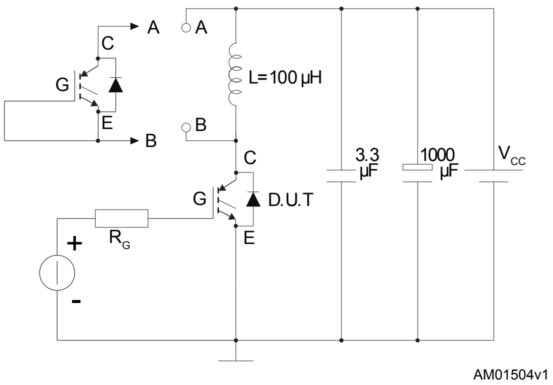


Figure 28. Gate charge test circuit

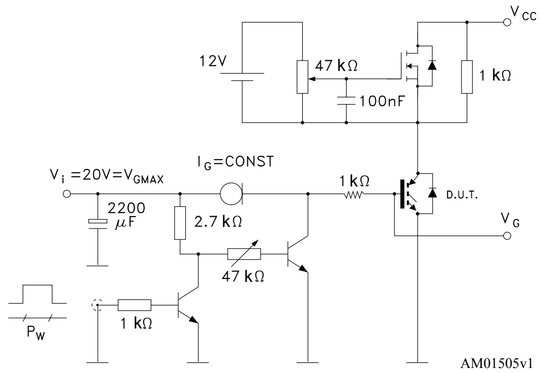


Figure 29. Switching waveform

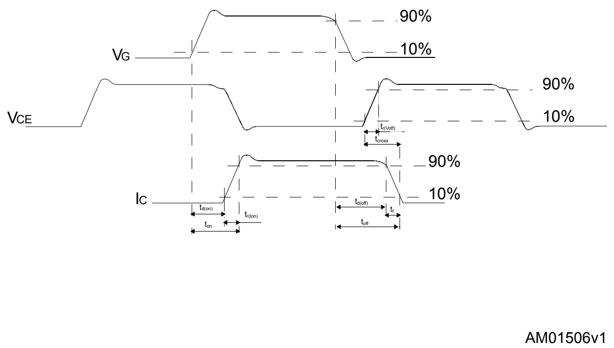
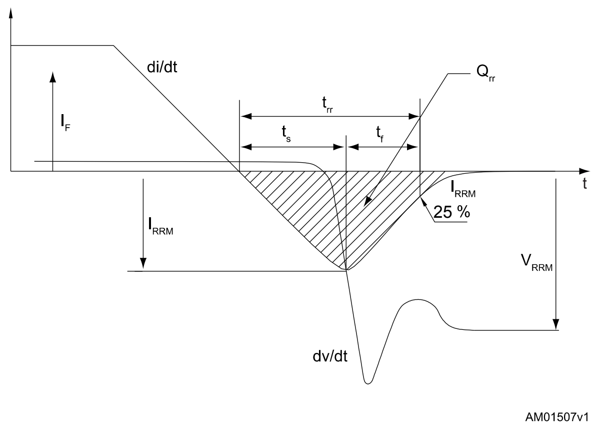


Figure 30. Diode reverse recovery waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-247 package information

Figure 31. TO-247 package outline

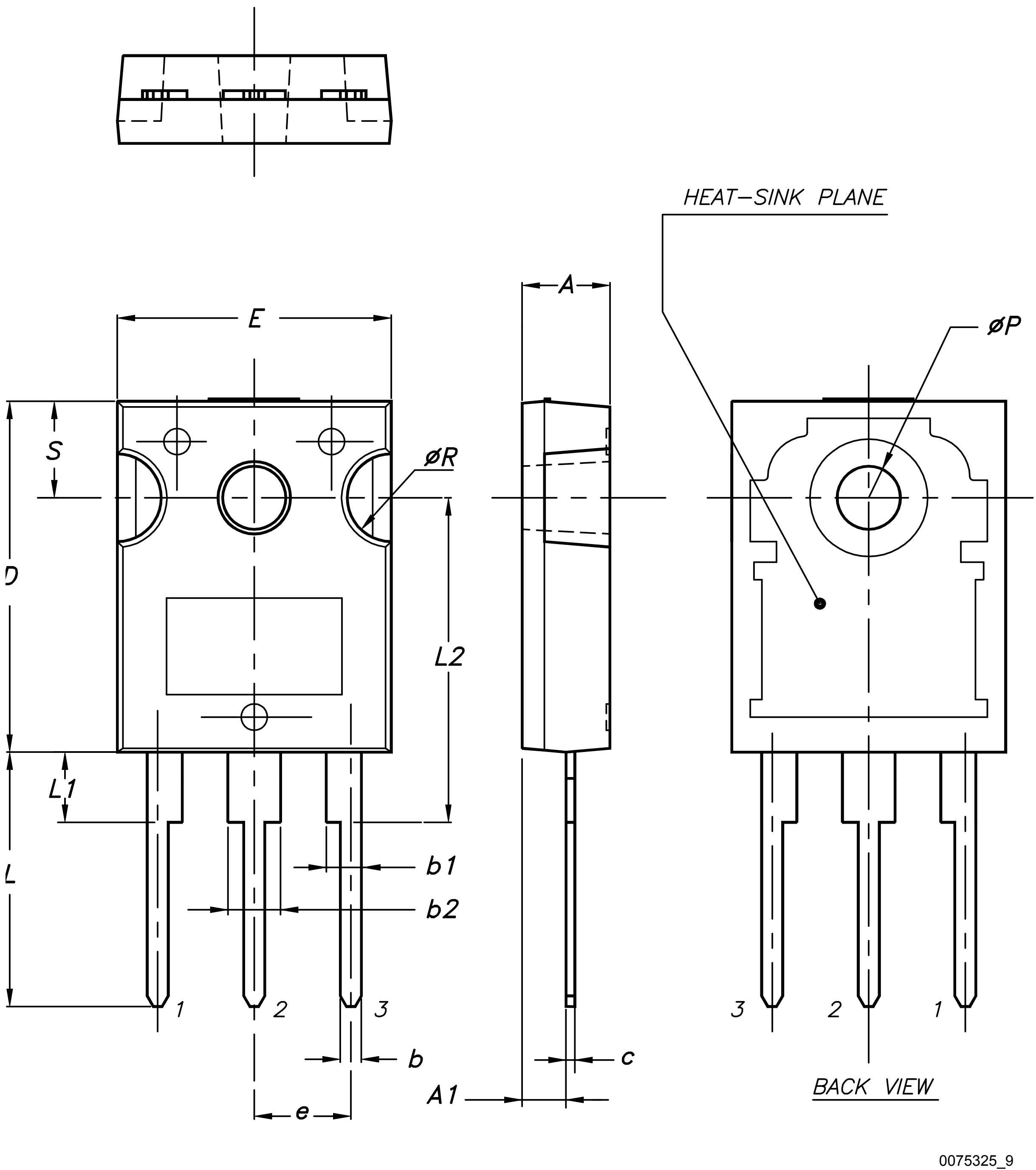


Table 7. TO-247 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

4.2 TO-247 long leads package information

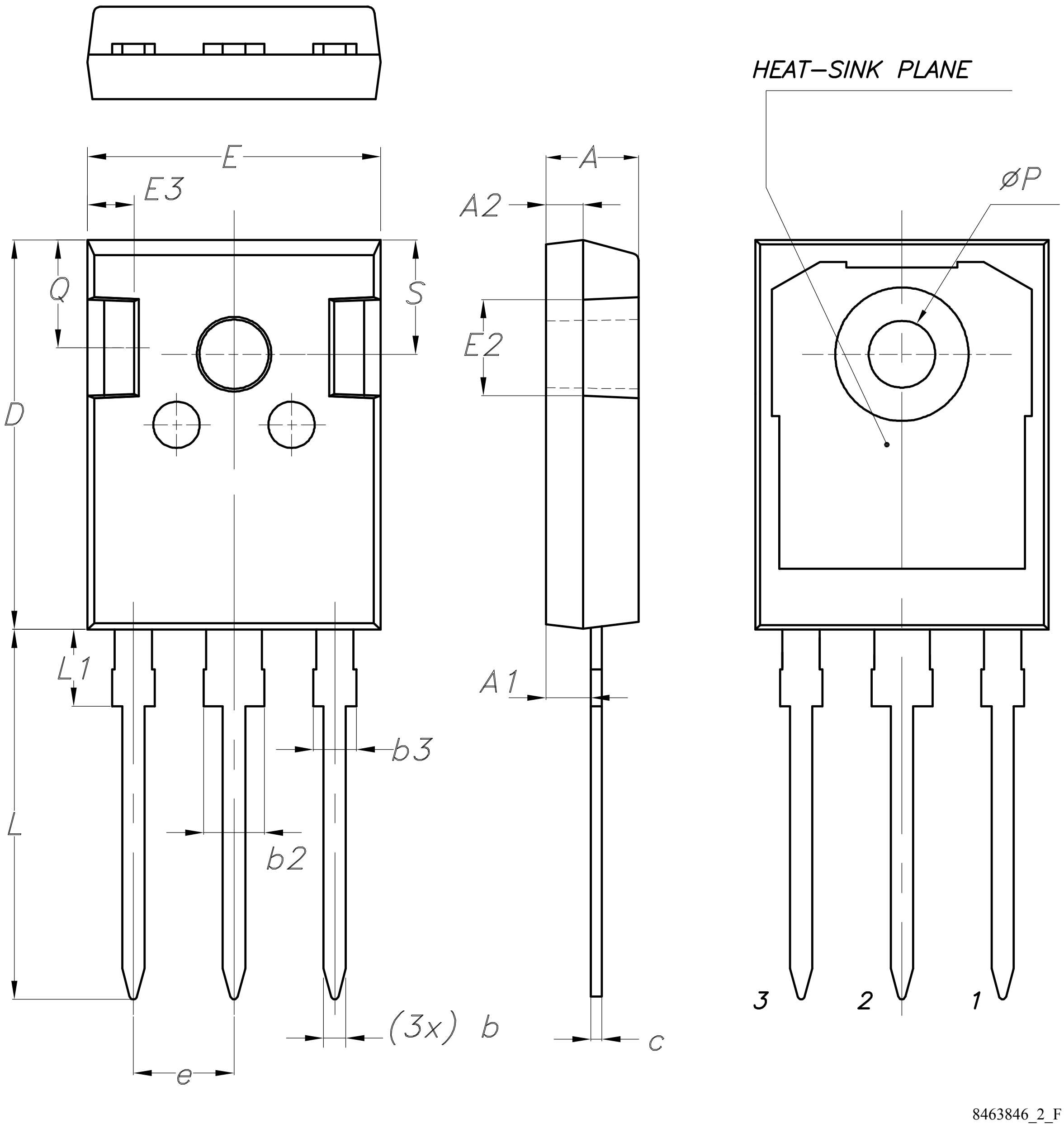


Figure 32. TO-247 long leads package outline

Table 8. TO-247 long leads package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.26
b2			3.25
b3			2.25
c	0.59		0.66
D	20.90	21.00	21.10
E	15.70	15.80	15.90
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	5.34	5.44	5.54
L	19.80	19.92	20.10
L1			4.30
P	3.50	3.60	3.70
Q	5.60		6.00
S	6.05	6.15	6.25

Revision history

Table 9. Document revision history

Date	Revision	Changes
03-Oct-2012	1	Initial release.
28-Feb-2014	2	Updated title and features in cover page. Minor text changes.
31-Mar-2014	3	Document status promoted from preliminary to production data. Updated *Table 4: Static characteristics* and *Table 6: IGBT switching characteristics (inductive load)*. Added Section 2.1: Electrical characteristics (curves).
06-Mar-2015	4	Added *4.2: TO-247 long leads, package information*. Minor text changes.
10-Mar-2021	5	Updated Table 1. Absolute maximum ratings. Minor text changes.

Contents